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What is "Embedded - Microcontrollers"?

"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "Embedded - Microcontrollers"

Details	
Product Status	Active
Core Processor	ARM® Cortex®-M4F
Core Size	32-Bit Single-Core
Speed	80MHz
Connectivity	CANbus, FlexIO, I²C, LINbus, SPI, UART/USART
Peripherals	POR, PWM, WDT
Number of I/O	89
Program Memory Size	512KB (512K x 8)
Program Memory Type	FLASH
EEPROM Size	4K x 8
RAM Size	64K x 8
Voltage - Supply (Vcc/Vdd)	2.7V ~ 5.5V
Data Converters	A/D 16x12b SAR; D/A1x8b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	100-LQFP
Supplier Device Package	100-LQFP (14x14)
Purchase URL	https://www.e-xfl.com/product-detail/nxp-semiconductors/fs32k144hrt0cllt

- Communications interfaces
  - Up to three Low Power Universal Asynchronous Receiver/Transmitter (LPUART/LIN) modules with DMA support and low power availability
  - Up to three Low Power Serial Peripheral Interface (LPSPI) modules with DMA support and low power availability
  - Up to two Low Power Inter-Integrated Circuit (LPI2C) modules with DMA support and low power availability
  - Up to three FlexCAN modules (with optional CAN-FD support)
  - FlexIO module for emulation of communication protocols and peripherals (UART, I2C, SPI, I2S, LIN, PWM, etc).
  - Up to one 10/100Mbps Ethernet with IEEE1588 support and two Synchronous Audio Interface (SAI) modules.
- Safety and Security
  - Cryptographic Services Engine (CSEc) implements a comprehensive set of cryptographic functions as described in the SHE (Secure Hardware Extension) Functional Specification. Note: CSEc (Security) or EEPROM writes/erase will trigger error flags in HSRUN mode (112 MHz) because this use case is not allowed to execute simultaneously. The device will need to switch to RUN mode (80 MHz) to execute CSEc (Security) or EEPROM writes/erase.
  - 128-bit Unique Identification (ID) number
  - Error-Correcting Code (ECC) on flash and SRAM memories
  - System Memory Protection Unit (System MPU)
  - Cyclic Redundancy Check (CRC) module
  - Internal watchdog (WDOG)
  - External Watchdog monitor (EWM) module
- Timing and control
  - Up to eight independent 16-bit FlexTimers (FTM) modules, offering up to 64 standard channels (IC/OC/PWM)
  - One 16-bit Low Power Timer (LPTMR) with flexible wake up control
  - Two Programmable Delay Blocks (PDB) with flexible trigger system
  - One 32-bit Low Power Interrupt Timer (LPIT) with 4 channels
  - 32-bit Real Time Counter (RTC)
- Package
  - 32-pin QFN, 48-pin LQFP, 64-pin LQFP, 100-pin LQFP, 100-pin MAPBGA, 144-pin LQFP, 176-pin LQFP package options
- 16 channel DMA with up to 63 request sources using DMAMUX

3 Ordering information

3.1 Selecting orderable part number

Not all part number combinations are available. See the attachment *S32K1xx_Orderable_Part_Number_ List.xlsx* attached with the Datasheet for a list of standard orderable part numbers.

4. When input pad voltage levels are close to V_{DD} or V_{SS}, practically no current injection is possible.
5. While respecting the maximum current injection limit
6. This is the Electronic Control Unit (ECU) supply ramp rate and not directly the MCU ramp rate. Limit applies to both maximum absolute maximum ramp rate and typical operating conditions.
7. This is the MCU supply ramp rate and the ramp rate assumes that the S32K1xx HW design guidelines in AN5426 are followed. Limit applies to both maximum absolute maximum ramp rate and typical operating conditions.
8. T_J (Junction temperature)=135 °C. Assumes T_A=125 °C for RUN mode

   T_J (Junction temperature)=125 °C. Assumes TA=105 °C for HSRUN mode

   - Assumes maximum θJA for 2s2p board. See Thermal characteristics
9. 60 seconds lifetime; device in reset (no outputs enabled/toggling)

4.2 Voltage and current operating requirements

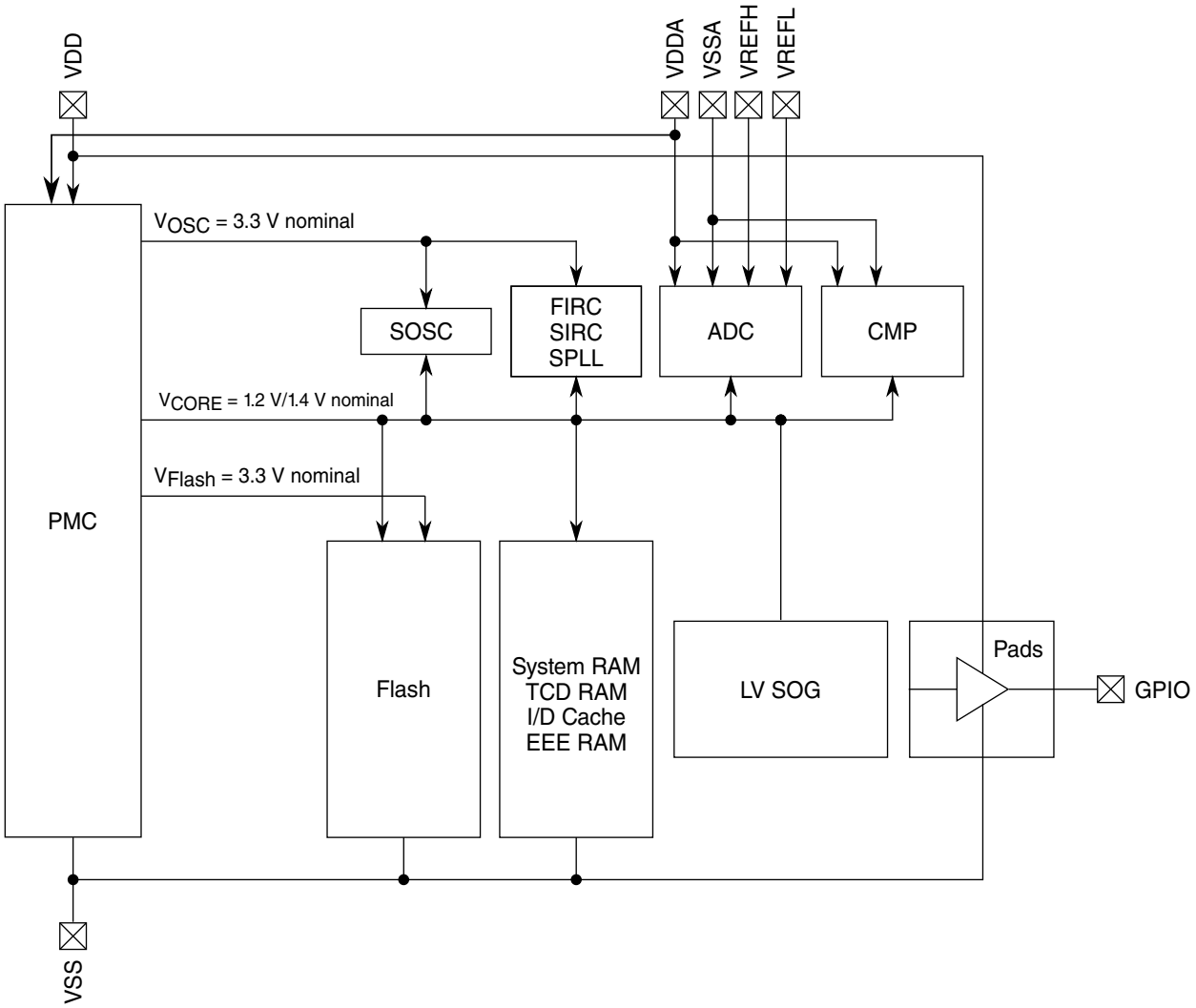
NOTE

Device functionality is guaranteed up to the LVR assert level, however electrical performance of 12-bit ADC, CMP with 8-bit DAC, IO electrical characteristics, and communication modules electrical characteristics would be degraded when voltage drops below 2.7 V

Table 2. Voltage and current operating requirements 1

Symbol	Description	Min.	Max.	Unit	Notes
V_{DD}[2]	Supply voltage	2.7[3]	5.5	V	4
V_{DD_OFF}	Voltage allowed to be developed on V_{DD} pin when it is not powered from any external power supply source.	0	0.1	V	
V_{DDA}	Analog supply voltage	2.7	5.5	V	4
$V_{DD} – V_{DDA}$	V_{DD}-to-V_{DDA} differential voltage	– 0.1	0.1	V	4
V_{REFH}	ADC reference voltage high	2.7	V_{DDA} + 0.1	V	5
V_{REFL}	ADC reference voltage low	-0.1	0.1	V	
V_{ODPU}	Open drain pullup voltage level	V_{DD}	V_{DD}	V	6
$I_{INJPAD\_DC\_OP}$[7]	Continuous DC input current (positive / negative) that can be injected into an I/O pin	-3	+3	mA	
$I_{INJSUM\_DC\_OP}$	Continuous total DC input current that can be injected across all I/O pins such that there's no degradation in accuracy of analog modules: ADC and ACMP (See section Analog Modules)	—	30	mA	

1. Typical conditions assumes V_{DD} = V_{DDA} = V_{REFH} = 5 V, temperature = 25 °C and typical silicon process unless otherwise stated.
2. As V_{DD} varies between the minimum value and the absolute maximum value the analog characteristics of the I/O and the ADC will both change. See section I/O parameters and ADC electrical specifications respectively for details.
3. S32K148 will operate from 2.7 V when executing from internal FIRC. When the PLL is engaged S32K148 is guaranteed to operate from 2.97 V. All other S32K family devices operate from 2.7 V in all modes.
4. V_{DD} and V_{DDA} must be shorted to a common source on PCB. The differential voltage between V_{DD} and V_{DDA} is for RF-AC only. Appropriate decoupling capacitors to be used to filter noise on the supplies. See application note AN5032 for reference supply design for SAR ADC.



*Note: VSSA and VSS are shorted at package level

Figure 6. Power diagram

4.5 LVR, LVD and POR operating requirements

Table 5. V_{DD} supply LVR, LVD and POR operating requirements

Symbol	Description	Min.	Typ.	Max.	Unit	Notes
V_{POR}	Rising and falling V_{DD} POR detect voltage	1.1	1.6	2.0	V	
V_{LVR}	LVR falling threshold (RUN, HSRUN, and STOP modes)	2.50	2.58	2.7	V	
V_{LVR_HYST}	LVR hysteresis	—	45	—	mV	1
V_{LVR_LP}	LVR falling threshold (VLPS/VLPR modes)	1.97	2.22	2.44	V	
V_{LVD}	Falling low-voltage detect threshold	2.8	2.875	3	V	
V_{LVD_HYST}	LVD hysteresis	—	50	—	mV	1

Table continues on the next page...

Table 6. Power mode transition operating behaviors (continued)

Symbol	Description	Min.	Typ.	Max.	Unit
	VLPS → RUN	8	—	17	µs
	STOP1 → RUN	0.07	0.075	0.08	µs
	STOP2 → RUN	0.07	0.075	0.08	µs
	VLPR → RUN	19	—	26	µs
	VLPR → VLPS	5.1	5.7	6.5	µs
	VLPS → VLPR	18.8	23	27.75	µs
	RUN → Compute operation	0.72	0.75	0.77	µs
	HSRUN → Compute operation	0.3	0.31	0.35	µs
	RUN → STOP1	0.35	0.38	0.4	µs
	RUN → STOP2	0.2	0.23	0.25	µs
	RUN → VLPS	0.3	0.35	0.4	µs
	RUN → VLPR	3.5	3.8	5	µs
	VLPS → Asynchronous DMA Wakeup	105	110	125	µs
	STOP1 → Asynchronous DMA Wakeup	1	1.1	1.3	µs
	STOP2 → Asynchronous DMA Wakeup	1	1.1	1.3	µs
	Pin reset → Code execution	—	214	—	µs

NOTE

HSRUN should only be used when frequencies in excess of 80 MHz are required. When using 80 MHz and below, RUN mode is the recommended operating mode.

4.7 Power consumption

The following table shows the power consumption targets for the device in various mode of operations. Attached *S32K1xx_Power_Modes _Configuration.xlsx* details the modes used in gathering the power consumption data stated in the following table Table 7. For full functionality refer to table: Module operation in available power modes of the *Reference Manual*.

Table 7. Power consumption (Typicals unless stated otherwise) 1

Chip/Device	Ambient Temperature (°C)		VLPS (µA) 2		VLPR (mA)			STOP1 (mA)	STOP2 (mA)	RUN@48 MHz (mA)		RUN@64 MHz (mA)		RUN@80 MHz (mA)		HSRUN@112 MHz (mA) 3		IDD/MHz (µA/MHz) 4
			Peripherals disabled 5	Peripherals enabled	Peripherals disabled 6	Peripherals enabled use case 1 6	Peripherals enabled use case 2 7			Peripherals disabled	Peripherals enabled	Peripherals disabled	Peripherals enabled	Peripherals disabled	Peripherals enabled	Peripherals disabled	Peripherals enabled	
S32K116	25	Typ	26	40	1.05	1.07	TBD	6.3	7.2	11.8	20.3	NA						245
	85	Typ	76	93	1.1	1.11	TBD	6.6	7.5	12	20.6							251
		Max	287	300	1.39	1.4	NA	8	8.9	13.4	22.1							279
	105	Typ	139	164	1.15	1.16	TBD	6.8	7.7	12.3	20.8							255
		Max	590	603	1.68	1.69	NA	9.2	10.1	14.5	23.1							302
	125	Typ	NA	NA	NA	NA	TBD	NA	NA	NA	NA							NA
		Max	891	904	2.02	2.04	NA	10.4	11.3	15.6	24.1							325
S32K118	25	Typ	26	38	1.9	2.5	TBD	7	12	TBD	TBD	NA						TBD
	105	Typ	TBD	TBD	TBD	TBD	TBD	TBD	TBD	TBD	TBD							TBD
		Max	TBD	TBD	TBD	TBD	TBD	TBD	TBD	TBD	TBD							TBD
	125	Max	TBD	TBD	TBD	TBD	TBD	TBD	TBD	TBD	42							TBD
S32K142	25	Typ	29	40	1.17	1.21	2.19	6.4	7.4	17.3	24.6	24.5	31.3	28.8	37.5	40.5	52.2	360
	85	Typ	128	137	1.48	1.51	2.31	7	8	17.6	24.9	25	31.6	29.1	37.7	41.1	52.5	364
		Max	335	360	1.87	1.89	NA	8.6	9.4	22	28.2	26.9	33.5	32	40	44	55.6	400
	105	Typ	240	257	1.58	1.61	2.44	7.6	8.3	18.3	25.7	25.5	31.9	29.8	38	41.5	53.1	373
		Max	740	791	2.32	2.34	NA	9.9	10.9	23.1	30.2	27.8	35.3	33.8	40.7	44.9	57.4	423
	125	Typ	NA	NA	NA	NA	2.84	NA	NA	NA	NA	NA	NA	NA	NA	NA		NA

Table continues on the next page...

Table 8. VLPS additional use-case power consumption at typical conditions

Use-case	Description	Temp.	Device						Unit
			S32K116	S32K118	S32K142	S32K144	S32K146	S32K148	
VLPS and RTC	• Clock source: LPO or RTC_CLKIN	25	TBD	TBD	30	30	30	40	µA
		85	TBD	TBD	110	170	180	240	µA
		105	TBD	TBD	230	330	350	490	µA
		125	TBD	TBD	570	680	810	1250	µA
VLPS and LPUART TX/RX	• Clock source: SIRC • Transmiting or receiving continuously using DMA • Baudrate: 19.2 kbps	25	TBD	TBD	230	230	250	250	µA
		85	TBD	TBD	320	400	410	490	µA
		105	TBD	TBD	490	550	600	850	µA
		125	TBD	TBD	890	1070	1250	1960	µA
VLPS and LPUART wake-up	• Clock source: SIRC • Wake-up address feature enabled • Baudrate: 19.2 kbps	25	TBD	TBD	100	100	110	110	µA
		85	TBD	TBD	170	240	280	350	µA
		105	TBD	TBD	260	400	480	600	µA
		125	TBD	TBD	530	580	1000	1280	µA
VLPS and LPI2C master	• Clock Source: SIRC • Transmit/receive using DMA • Baudrate: 100 kHz	25	TBD	TBD	670	690	820	900	µA
		85	TBD	TBD	880	960	1220	1370	µA
		105	TBD	TBD	1080	1250	1660	2060	µA
		125	TBD	TBD	1970	1980	2860	3690	µA
VLPS and LPI2C slave wake-up	• Clock source: SIRC • Wake-up address feature enabled • Baudrate: 100 kHz	25	TBD	TBD	250	250	270	280	µA
		85	TBD	TBD	340	340	410	510	µA
		105	TBD	TBD	430	430	610	810	µA
		125	TBD	TBD	740	760	1170	1540	µA
VLPS and LPSPI master	• Clock source: SIRC • Transmit/receive using DMA • Baudrate: 500 kHz	25	TBD	TBD	2.99	3.19	3.75	4.11	mA
		85	TBD	TBD	3.26	3.7	4.35	4.93	mA
		105	TBD	TBD	3.5	4.2	4.93	5.74	mA
		125	TBD	TBD	3.93	4.63	5.97	7.38	mA
VLPS and LPIT	• Clock source: SIRC • 1 channel enable • Mode: 32-bit periodic counter	25	TBD	TBD	100	100	120	130	µA
		85	TBD	TBD	190	250	260	320	µA
		105	TBD	TBD	310	410	440	570	µA
		125	TBD	TBD	640	750	910	1280	µA

5.3 DC electrical specifications at 3.3 V Range

NOTE

For details on the pad types defined in Table 11 and Table 12, see Reference Manual section *IO Signal Table* and IO Signal Description Input Multiplexing sheet(s) attached with Reference Manual.

Table 11. DC electrical specifications at 3.3 V Range

Symbol	Parameter	Value			Unit	Notes
		Min.	Typ.	Max.		
V_{DD}	I/O Supply Voltage	2.7	3.3	4	V	1
V_{ih}	Input Buffer High Voltage	0.7 × V_{DD}	—	V_{DD} + 0.3	V	2
V_{il}	Input Buffer Low Voltage	V_{SS} – 0.3	—	0.3 × V_{DD}	V	3
V_{hys}	Input Buffer Hysteresis	0.06 × V_{DD}	—	—	V	
Ioh_{GPIO} $Ioh_{GPIO\text{-}HD\_DSE\_0}$	I/O current source capability measured when pad V_{oh} = (V_{DD} – 0.8 V)	3.5	—	—	mA	
Iol_{GPIO} $Iol_{GPIO\text{-}HD\_DSE\_0}$	I/O current sink capability measured when pad V_{ol} = 0.8 V	3	—	—	mA	
$Ioh_{GPIO\text{-}HD\_DSE\_1}$	I/O current source capability measured when pad V_{oh} = (V_{DD} – 0.8 V)	14	—	—	mA	4
$Iol_{GPIO\text{-}HD\_DSE\_1}$	I/O current sink capability measured when pad V_{ol} = 0.8 V	12	—	—	mA	4
$Ioh_{GPIO\text{-}FAST\_DSE\_0}$	I/O current sink capability measured when pad V_{oh}=V_{DD}-0.8 V	9.5	—	—	mA	5
$Iol_{GPIO\text{-}FAST\_DSE\_0}$	I/O current sink capability measured when pad V_{ol} = 0.8 V	10	—	—	mA	5
$Ioh_{GPIO\text{-}FAST\_DSE\_1}$	I/O current sink capability measured when pad V_{oh}=V_{DD}-0.8 V	16	—	—	mA	5
$Iol_{GPIO\text{-}FAST\_DSE\_1}$	I/O current sink capability measured when pad V_{ol} = 0.8 V	15.5	—	—	mA	5
IOHT	Output high current total for all ports	—	—	100	mA	
IIN	Input leakage current (per pin) for full temperature range at V_{DD} = 3.3 V					6
	All pins other than high drive port pins		0.005	0.5	µA	
	High drive port pins [7]		0.010	0.5	µA	
R_{PU}	Internal pullup resistors	20		60	kΩ	8
R_{PD}	Internal pulldown resistors	20		60	kΩ	9

1. S32K148 will operate from 2.7 V when executing from internal FIRC. When the PLL is engaged S32K148 is guaranteed to operate from 2.97 V. All other S32K family devices operate from 2.7 V in all modes.
2. For reset pads, same V_{ih} levels are applicable
3. For reset pads, same V_{il} levels are applicable
4. The value given is measured at high drive strength mode. For value at low drive strength mode see the Ioh_Standard value given above.
5. For refernce only. Run simulations with the IBIS model and custom board for accurate results.

5. Several I/O have both high drive and normal drive capability selected by the associated Portx_PCRn[DSE] control bit. All other GPIOs are normal drive only. For details refer to *SK3K144_IO_Signal_Description_Input_Multiplexing.xlsx* attached with the *Reference Manual*.
6. Measured at input V = V_{SS}
7. Measured at input V = V_{DD}

5.5 AC electrical specifications at 3.3 V range

Table 13. AC electrical specifications at 3.3 V Range

Symbol	DSE	Rise time (nS) [1]		Fall time (nS) [1]		Capacitance (pF) [2]
		Min.	Max.	Min.	Max.	
tRF_{GPIO}	NA	3.2	14.5	3.4	15.7	25
		5.7	23.7	6.0	26.2	50
		20.0	80.0	20.8	88.4	200
$tRF_{GPIO-HD}$	0	3.2	14.5	3.4	15.7	25
		5.7	23.7	6.0	26.2	50
		20.0	80.0	20.8	88.4	200
	1	1.5	5.8	1.7	6.1	25
		2.4	8.0	2.6	8.3	50
		6.3	22.0	6.0	23.8	200
$tRF_{GPIO-FAST}$	0	0.6	2.8	0.5	2.8	25
		3.0	7.1	2.6	7.5	50
		12.0	27.0	10.3	26.8	200
	1	0.4	1.3	0.38	1.3	25
		1.5	3.8	1.4	3.9	50
		7.4	14.9	7.0	15.3	200

1. For reference only. Run simulations with the IBIS model and your custom board for accurate results.
2. Maximum capacitances supported on Standard IOs. However interface or protocol specific specifications might be different, for example for ENET, QSPI etc. . For protocol specific AC specifications, see respective sections.

5.6 AC electrical specifications at 5 V range

Table 14. AC electrical specifications at 5 V Range

Symbol	DSE	Rise time (nS)[1]		Fall time (nS) [1]		Capacitance (pF) [2]
		Min.	Max .	Min.	Max.	
tRF_{GPIO}	NA	2.8	9.4	2.9	10.7	25
		5.0	15.7	5.1	17.4	50
		17.3	54.8	17.6	59.7	200
$tRF_{GPIO-HD}$	0	2.8	9.4	2.9	10.7	25
		5.0	15.7	5.1	17.4	50

Table continues on the next page...

Table 23. Flash command timing specifications for S32K14x (continued)

Symbol	Description[1]		S32K142		S32K144		S32K146		S32K148			
			Typ	Max	Typ	Max	Typ	Max	Typ	Max	Unit	Notes
t_{setram}	Set FlexRAM Function execution time	Control Code 0xFF	0.08	—	0.08	—	0.08	—	0.08	—	ms	3
		32 KB EEPROM backup	0.8	1.2	0.8	1.2	0.8	1.2	—	—		
		48 KB EEPROM backup	1	1.5	1	1.5	1	1.5	—	—		
		64 KB EEPROM backup	1.3	1.9	1.3	1.9	1.3	1.9	1.3	1.9		
t_{eewr8b}	Byte write to FlexRAM execution time	32 KB EEPROM backup	385	1700	385	1700	385	1700	—	—	µs	3,4
		48 KB EEPROM backup	430	1850	430	1850	430	1850	—	—		
		64 KB EEPROM backup	475	2000	475	2000	475	2000	475	4000		
$t_{eewr16b}$	16-bit write to FlexRAM execution time	32 KB EEPROM backup	385	1700	385	1700	385	1700	—	—	µs	3,4
		48 KB EEPROM backup	430	1850	430	1850	430	1850	—	—		
		64 KB EEPROM backup	475	2000	475	2000	475	2000	475	4000		
$t_{eewr32bers}$	32-bit write to erased FlexRAM location execution time	—	360	2000	360	2000	360	2000	360	2000	µs	
$t_{eewr32b}$	32-bit write to FlexRAM execution time	32 KB EEPROM backup	630	2000	630	2000	630	2000	—	—	µs	3,4
		48 KB EEPROM backup	720	2125	720	2125	720	2125	—	—		
		64 KB EEPROM backup	810	2250	810	2250	810	2250	810	4500		
$t_{quickwr}$	32-bit Quick Write execution time: Time from CCIF clearing (start the write) until CCIF	1st 32-bit write	200	550	200	550	200	550	200	1100	µs	4,5,6
		2nd through Next to Last (Nth-1) 32-bit write	150	550	150	550	150	550	150	550		

Table continues on the next page...

Table 23. Flash command timing specifications for S32K14x (continued)

Symbol	Description[1]		S32K142		S32K144		S32K146		S32K148			
			Typ	Max	Typ	Max	Typ	Max	Typ	Max	Unit	Notes
	setting (32-bit write complete, ready for next 32-bit write)	Last (Nth) 32-bit write (time for write only, not cleanup)	200	550	200	550	200	550	200	550		
$t_{quickwrClnup}$	Quick Write Cleanup execution time	—	—	(# of Quick Writes) * 2.0	—	(# of Quick Writes) * 2.0	—	(# of Quick Writes) * 2.0	—	(# of Quick Writes) * 2.0	ms	7

1. All command times assumes 25 MHz or greater flash clock frequency (for synchronization time between internal/external clocks).
2. Maximum times for erase parameters based on expectations at cycling end-of-life.
3. For all EEPROM Emulation terms, the specified timing shown assumes previous record cleanup has occurred. This may be verified by executing FCCOB Command 0x77, and checking FCCOB number 5 contents show 0x00 - No EEPROM issues detected.
4. 1st time EERAM writes after a Reset or SETRAM may incur additional overhead for EEE cleanup, resulting in up to 2× the times shown.
5. Only after the Nth write completes will any data be valid. Emulated EEPROM record scheme cleanup overhead may occur after this point even after a brownout or reset. If power on reset occurs before the Nth write completes, the last valid record set will still be valid and the new records will be discarded.
6. Quick Write times may take up to 550 µs, as additional cleanup may occur when crossing sector boundaries.
7. Time for emulated EEPROM record scheme overhead cleanup. Automatically done after last (Nth) write completes, assuming still powered. Or via SETRAM cleanup execution command is requested at a later point.

Table 24. Flash command timing specifications for S32K11x

Symbol	Description[1]		S32K116		S32K118			
			Typ	Max	Typ	Max	Unit	Notes
t_{rd1blk}	Read 1 Block execution time	32 KB flash	—	0.36	—	0.36	ms	
		64 KB flash	—	—	—	—		
		128 KB flash	—	1.2	—	—		
		256 KB flash	—	—	—	2		
		512 KB flash	—	—	—	—		
t_{rd1sec}	Read 1 Section execution time	2 KB flash	—	75	—	75	µs	
		4 KB flash	—	100	—	100		
t_{pgmchk}	Program Check execution time	—	—	100	—	100	µs	
t_{pgm8}	Program Phrase execution time	—	90	225	90	225	µs	
t_{ersblk}	Erase Flash Block execution time	32 KB flash	15	300	15	300	ms	2
		64 KB flash	—	—	—	—		
		128 KB flash	120	1100	—	—		
		256 KB flash	—	—	250	2125		
		512 KB flash	—	—	—	—		

Table continues on the next page...

Table 26. QuadSPI electrical specifications

FLASH PORT	Sym	Unit	FLASH A												FLASH B			
			RUN[1]						HSRUN[1]						RUN/HSRUN[2]			
QuadSPI Mode			SDR						SDR						SDR		DDR[3]	
			Internal Sampling		Internal DQS				Internal Sampling		Internal DQS				Internal Sampling		External DQS	
			N1		PAD Loopback		Internal Loopback		N1		PAD Loopback		Internal Loopback		N1		External DQS	
			Min	Max	Min	Max	Min	Max	Min	Max	Min	Max	Min	Max	Min	Max	Min	Max
Register Settings																		
MCR[DDR_EN]		-	0		0		0		0		0		0		0		1	
MCR[DQS_EN]		-	0		1		1		0		1		1		0		1	
MCR[SCLKCFG[0]]		-	-		1		0		-		1		0		-		-	
MCR[SCLKCFG[1]]		-	-		1		0		-		1		0		-		-	
MCR[SCLKCFG[2]]		-	-		-		-		-		-		-		-		0	
MCR[SCLKCFG[3]]		-	-		-		-		-		-		-		-		0	
MCR[SCLKCFG[5]]		-	0		0		0		0		0		0		0		1	
SMPR[FSPHS]		-	0		1		0		0		1		0		0		0	
SMPR[FSDLY]		-	0		0		0		0		0		0		0		0	
SOCCR [SOCCFG[7:0]]			-		0		23		-		0		30		-		-	
SOCCR[SOCCFG[15:8]]		-	-		-		-		-		-		-		-		30	
FLSHCR[TDH]		-	0x00		0x00		0x00		0x00		0x00		0x00		0x00		0x01	
Timing Parameters																		
SCK Clock Frequency	f_{SCK}	MHz	-	38	-	64	-	48	-	40	-	80	-	50	-	20	-	20[4]
SCK Clock Period	t_{SCK}	ns	1/fSCK	-	1/fSCK	-	1/fSCK	-	1/fSCK	-	1/fSCK	-	1/fSCK	-	50.0	-	50.0[4]	-

Table continues on the next page...

Table 27. 12-bit ADC operating conditions (continued)

Symbol	Description	Conditions	Min.	Typ.[1]	Max.	Unit	Notes
f_{ADCK}	ADC conversion clock frequency	Normal usage	2	40	50	MHz	3, 4
f_{CONV}	ADC conversion frequency	No ADC hardware averaging.[5] Continuous conversions enabled, subsequent conversion time	46.4	928	1160	Ksps	6, 7
		ADC hardware averaging set to 32. [5] Continuous conversions enabled, subsequent conversion time	1.45	29	36.25	Ksps	6, 7

1. Typical values assume V_{DDA} = 5 V, Temp = 25 °C, f_{ADCK} = 40 MHz, R_{AS}=20 Ω, and C_{AS}=10 nF unless otherwise stated. Typical values are for reference only, and are not tested in production.
2. For packages without dedicated V_{REFH} and V_{REFL} pins, V_{REFH} is internally tied to V_{DDA}, and V_{REFL} is internally tied to V_{SS}. To get maximum performance, reference supply quality should be better than SAR ADC. See application note AN5032 for details.
3. Clock and compare cycle need to be set according to the guidelines mentioned in the *Reference Manual* .
4. ADC conversion will become less reliable above maximum frequency.
5. When using ADC hardware averaging, see the *Reference Manual* to determine the most appropriate setting for AVGS.
6. Numbers based on the minimum sampling time of 275 ns.
7. For guidelines and examples of conversion rate calculation, see the *Reference Manual* section 'Calibration function'

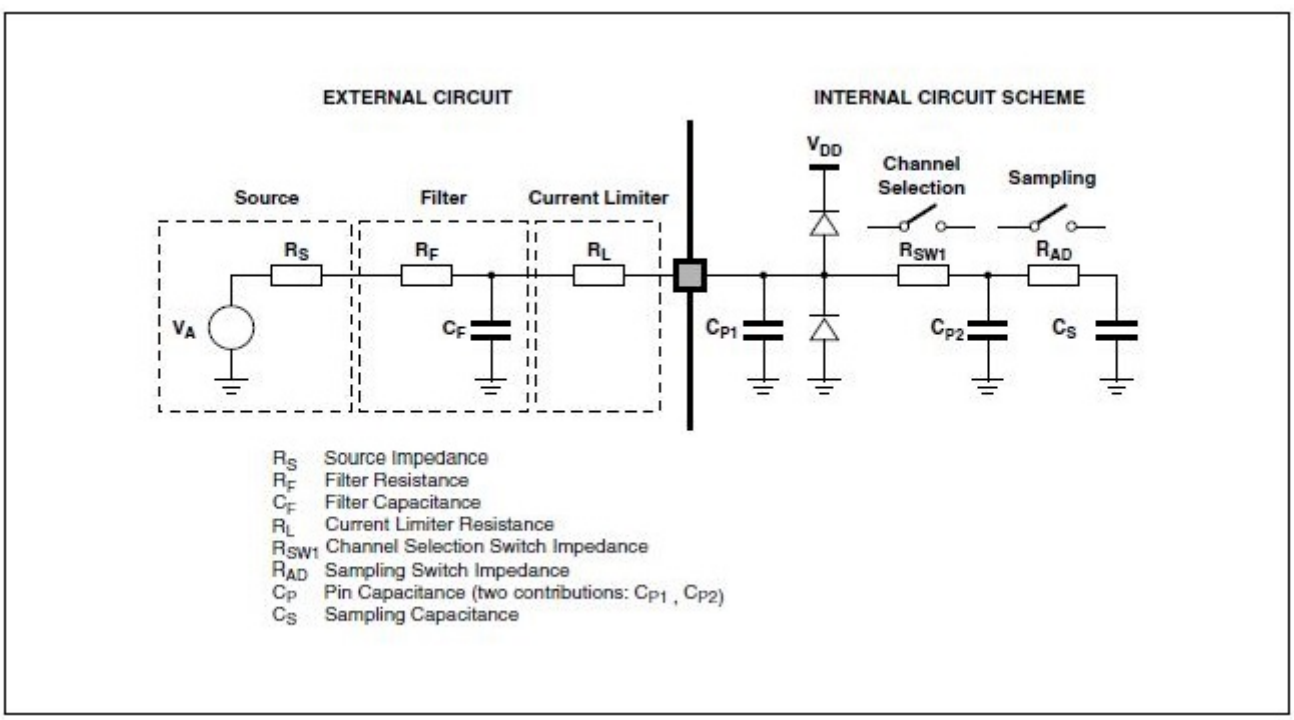


Figure 13. ADC input impedance equivalency diagram

Table 29. 12-bit ADC characteristics (3 V to 5.5 V)(V_{REFH} = V_{DDA}, V_{REFL} = V_{SS})

Symbol	Description	Conditions [1]	Min.	Typ.[2]	Max.	Unit	Notes
V_{DDA}	Supply voltage		3	—	5.5	V	
I_{DDA_ADC}	Supply current per ADC		—	1	—	mA	3
SMPLTS	Sample Time		275	—	Refer to the *Reference Manual*	ns	
TUE[4]	Total unadjusted error		—	±4	±8	LSB[5]	6, 7, 8, 9
DNL	Differential non-linearity		—	±0.7	—	LSB[5]	6, 7, 8, 9
INL	Integral non-linearity		—	±1.0	—	LSB[5]	6, 7, 8, 9

1. All accuracy numbers assume the ADC is calibrated with V_{REFH}=V_{DDA}=V_{DD}, with the calibration frequency set to less than or equal to half of the maximum specified ADC clock frequency.
2. Typical values assume V_{DDA} = 5.0 V, Temp = 25 °C, f_{ADCK} = 40 MHz, R_{AS}=20 Ω, and C_{AS}=10 nF unless otherwise stated.
3. The ADC supply current depends on the ADC conversion rate.
4. Represents total static error, which includes offset and full scale error.
5. 1 LSB = (V_{REFH} - V_{REFL})/2^N
6. The specifications are with averaging and in standalone mode only. Performance may degrade depending upon device use case scenario. When using ADC averaging, refer to the *Reference Manual* to determine the most appropriate settings for AVGS.
7. For ADC signals adjacent to V_{DD}/V_{SS} or XTAL/EXTAL or high frequency switching pins, some degradation in the ADC performance may be observed.
8. All values guarantee the performance of the ADC for multiple ADC input channel pins. When using ADC to monitor the internal analog parameters, assume minor degradation.
9. All the parameters in the table are given assuming system clock as the clocking source for ADC.

NOTE

- Due to triple bonding in lower pin packages like 32-QFN, 48-LQFP, and 64-LQFP degradation might be seen in ADC parameters.
- When using high speed interfaces such as the QuadSPI, SAI0, SAI1 or ENET there may be some ADC degradation on the adjacent analog input paths. See following table for details.

Pin name	TGATE purpose
PTE8	CMP0_IN3
PTC3	ADC0_SE11/CMP0_IN4
PTC2	ADC0_SE10/CMP0_IN5
PTD7	CMP0_IN6
PTD6	CMP0_IN7
PTD28	ADC1_SE22
PTD27	ADC1_SE21

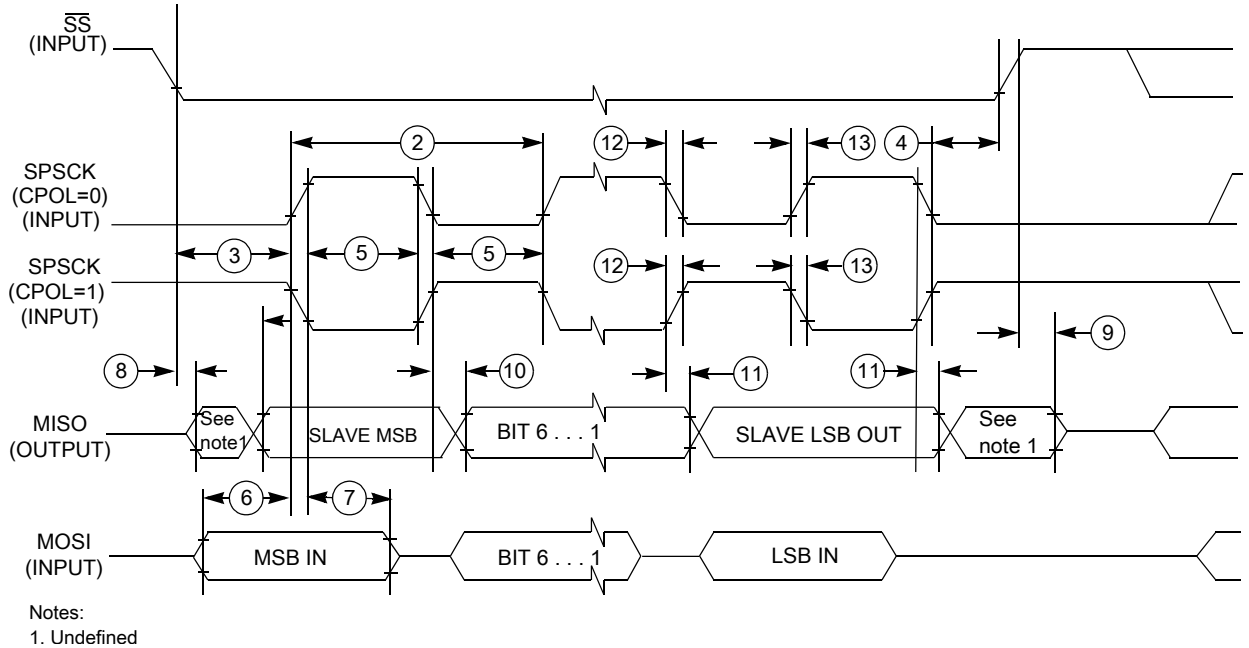


Figure 20. LPSPI slave mode timing (CPHA = 0)

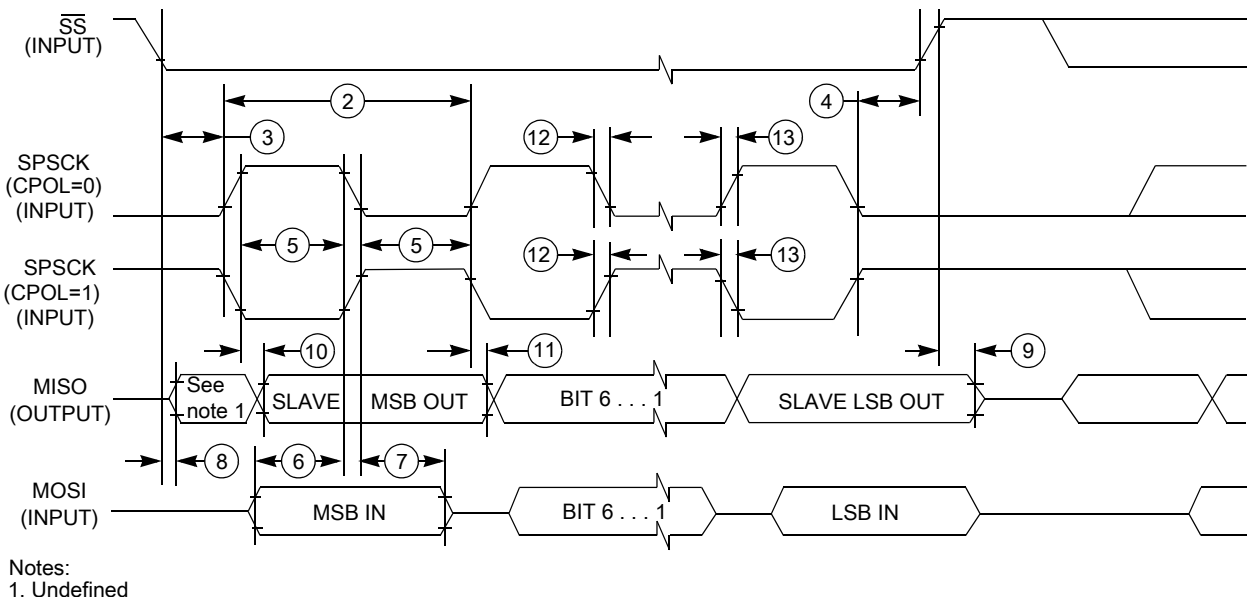


Figure 21. LPSPI slave mode timing (CPHA = 1)

6.5.3 LPI2C electrical specifications

See General AC specifications for LPI2C specifications.

For supported baud rate see section 'Chip-specific LPI2C information' of the *Reference Manual.*

Table 37. MDIO timing specifications (continued)

Symbol	Description	Min.	Max.	Unit
MDC1	MDC pulse width high	40%	60%	MDC period
MDC2	MDC pulse width low	40%	60%	MDC period
MDC3	MDIO (input) to MDC rising edge setup	25	—	ns
MDC4	MDIO (input) to MDC rising edge hold	0	—	ns
MDC5	MDC falling edge to MDIO output valid (maximum propagation delay)	—	25	ns
MDC6	MDC falling edge to MDIO output invalid (minimum propagation delay)	-10	—	ns

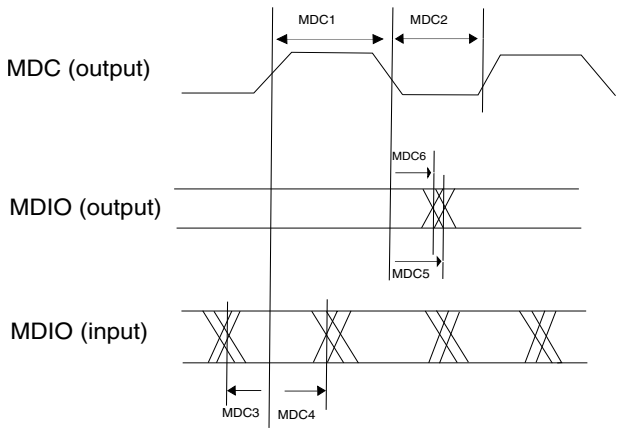


Figure 28. MII/RMII serial management channel timing diagram

6.5.7 Clockout frequency

Maximum supported clock out frequency for this device is 20 MHz

6.6 Debug modules

6.6.1 SWD electrical specofications

Table 41. Thermal characteristics for 32-pin QFN and 48/64/100/144/176-pin LQFP package (continued)

Rating	Conditions	Symbol	Package	Values						Unit
				S32K116	S32K118	S32K142	S32K144	S32K146	S32K148	
Thermal resistance, Junction to Package Top[7]	Natural Convection	Ψ_{JT}	32	1	NA	NA	NA	NA	NA	
			48	4	2	NA	NA	NA	NA	
			64	NA	2	2	2	2	NA	
			100	NA	NA	2	2	2	NA	
			144	NA	NA	NA	NA	2	1	
			176	NA	NA	NA	NA	NA	1	

1. Junction temperature is a function of die size, on-chip power dissipation, package thermal resistance, mounting site (board) temperature, ambient temperature, air flow, power dissipation of other components on the board, and board thermal resistance.
2. Per JEDEC JESD51-2 with natural convection for horizontally oriented board. Board meets JESD51-9 specification for 1s or 2s2p board, respectively.
3. Per JEDEC JESD51-6 with forced convection for horizontally oriented board. Board meets JESD51-9 specification for 1s or 2s2p board, respectively.
4. Thermal resistance between the die and the printed circuit board per JEDEC JESD51-8. Board temperature is measured on the top surface of the board near the package.
5. Thermal resistance between the die and the case top surface as measured by the cold plate method (MIL SPEC-883 Method 1012.1).
6. Thermal resistance between the die and the solder pad on the bottom of the package. Interface resistance is ignored.
7. Thermal characterization parameter indicating the temperature difference between package top and the junction temperature per JEDEC JESD51-2. When Greek letters are not available, the thermal characterization parameter is written as Psi-JT.

7.3 General notes for specifications at maximum junction temperature

An estimation of the chip junction temperature, T_J, can be obtained from this equation:

$$T_J = T_A + (R_{\theta JA} \times P_D)$$

where:

- T_A = ambient temperature for the package (°C)
- $R_{\theta JA}$ = junction to ambient thermal resistance (°C/W)
- P_D = power dissipation in the package (W)

The junction to ambient thermal resistance is an industry standard value that provides a quick and easy estimation of thermal performance. Unfortunately, there are two values in common usage: the value determined on a single layer board and the value obtained on a board with two planes. For packages such as the PBGA, these values can be different by a factor of two. Which value is closer to the application depends on the power dissipated by other components on the board. The value obtained on a single layer board is appropriate for the tightly packed printed circuit board. The value obtained on the board with the internal planes is usually appropriate if the board has low power dissipation and the components are well separated.

When a heat sink is used, the thermal resistance is expressed in the following equation as the sum of a junction-to-case thermal resistance and a case-to-ambient thermal resistance:

$$R_{\theta JA} = R_{\theta JC} + R_{\theta CA}$$

where:

- $R_{\theta JA}$ = junction to ambient thermal resistance (°C/W)
- $R_{\theta JC}$ = junction to case thermal resistance (°C/W)
- $R_{\theta CA}$ = case to ambient thermal resistance (°C/W)

$R_{\theta JC}$ is device related and cannot be influenced by the user. The user controls the thermal environment to change the case to ambient thermal resistance, $R_{\theta CA}$. For instance, the user can change the size of the heat sink, the air flow around the device, the interface material, the mounting arrangement on printed circuit board, or change the thermal dissipation on the printed circuit board surrounding the device.

Table 43. Revision History (continued)

Rev. No.	Date	Substantial Changes
		• Fixed the typo in R_{SW1} • In LPSPI electrical specifications : • Updated t_{Lead} and t_{Lag} • Added footnote in Figure: LPSPI slave mode timing (CPHA = 0) and Figure: LPSPI slave mode timing (CPHA = 1) • In Thermal characteristics : • Updated the name of table: Thermal characteristics for 32-pin QFN and 48/64/100/144/176-pin LQFP package • Deleted specs for $R_{\theta JC}$ for 32 QFN package • Added '$R_{\theta JCBottom}$'
8	18 June 2018	• In attachement '*S32K1xx_Power_Modes _Configuration*': • Updated VLPR peripherals disabled and Peripherals Enabled use case #1, using 4 Mhz for System clock, 2 Mhz for bus clock, and 1Mhz for flash. • Removed S32K116 from Notes • In figure: S32K1xx product series comparison : • Added note 'Availability of peripherals depends on the pin availability ...' • Updated 'Ambient Operation Temperature' row • Updated 'System RAM (including FlexRAM and MTB)' row for S32K144, S32K146, and S32K148 • In Ordering information : • Updated figure for 'Y: Optional feature' • Updated footnote 3 • In Power and ground pins : • In figure 'Power diagram', updtaed V_{Flash} frequency to 3.3 V • In Power mode transition operating behaviors : • Updated footnote for 'VLPS Mode: All clock sources disabled' • In Power consumption : • Added IDDs for S32K116 • Added VLPR Peripherals enabled use case 2 at 125 °C/Typicals • Renamed VLPR 'Peripherals enabled' to 'Peripherals enabled use case 1' • Added footnote 'Data collected using RAM' to VLPR 'Peripherals disabled' and VLPR 'Peripherals enabled use case 1' • Updated VLPS Peripherals enabled at 25 °C/Typicals for S32K142 and S32K144 to 40 µA and 42 µA respectively • Added table 'VLPS additional use-case power consumption at typical conditions' • In DC electrical specifications at 3.3 V Range : • Updated naming conventions • Added specs for GPIO-FAST pad • In DC electrical specifications at 5.0 V Range : • Updated naming conventions • Added specs for GPIO-FAST pad • In AC electrical specifications at 3.3 V range : • Updated naming conventions • Added specs for GPIO-FAST pad • In AC electrical specifications at 5 V range : • Updated naming conventions • Added specs for GPIO-FAST pad • In External System Oscillator electrical specifications : • Clarified description of g_{mXOSC} • Updated V_{IL} max. to 1.15 V • In Fast internal RC Oscillator (FIRC) electrical specifications :

Table 43. Revision History

Rev. No.	Date	Substantial Changes
		• Updated specs for T_{JIT} Cycle-to-Cycle jitter to 300 ps • In QuadSPI AC specifications : • Updated specs for T_{iv} Data Output In-Valid Time • In figure 'QuadSPI output timing (SDR mode) diagram', marked Invalid area • In CMP with 8-bit DAC electrical specifications : • Removed '(VAIO)' from decription of V_{HYST0} • In LPSPI electrical specifications : • Added note 'Undefined' in figures 'LPSPI slave mode timing (CPHA = 0)' and 'LPSPI slave mode timing (CPHA = 1)'